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Attorney Docket No.: 5308-413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

AUG 26 2004

In re: Saxler et al.

Application No.: 10/849,617

Filed: May 20, 2004

Confirmation No.: 9882

Group Art Unit: 2811

Examiner: Unknown

For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING
REGROWN OHMIC CONTACT REGIONS AND NITRIDE-BASED TRANSISTORS
HAVING REGROWN OHMIC CONTACT REGIONS

Date: August 24, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

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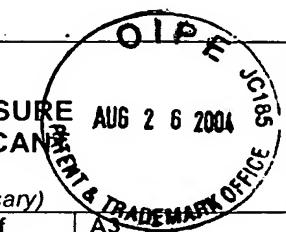
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Erin A. Campion

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet



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of

A3

		Complete if Known	
		Application Number	10/849,617
		Filing Date	May 20, 2004
		First Named Inventor	Saxler
		Group Art Unit	2811
		Examiner Name	To Be Assigned
		Attorney Docket Number	5308-413

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
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Examiner Signature

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
Sheet	A2	of	A3	Application Number	10/849,617
				Filing Date	May 20, 2004
				First Named Inventor	Saxler
				Group Art Unit	2811
				Examiner Name	To Be Assigned
				Attorney Docket Number	5308-392

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
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Examiner Signature _____ Date Considered _____

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OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
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